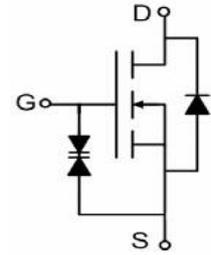


## 60V N-Channel Enhancement Mode MOSFET

### Description

The AP2N7002AI uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

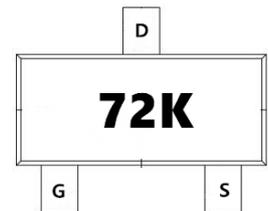


### General Features

$V_{DS} = 60V$   $I_D = 0.3A$

$R_{DS(ON)} < 3\Omega$  @  $V_{GS} = 10V$

ESD Rating: HBM  $\geq 2000V$



### Application

Battery protection

Load switch

Uninterruptible power supply



### Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
AP2N7002AI	SOT23L	72K	3000

### Absolute Maximum Ratings ( $T_C = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	60	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current ( $T_J = 150^\circ C$ )	$I_D$	$T_A = 25^\circ C$	0.3
		$T_A = 100^\circ C$	0.19
Drain Current-Pulsed (Note 1)	$I_{DM}$	0.8	A
Maximum Power Dissipation	$P_D$	0.35	W
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 150	$^\circ C$
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	350	$^\circ C/W$

## 60V N-Channel Enhancement Mode MOSFET

### Electrical Characteristics ( $T_A=25^\circ\text{C}$ unless otherwise noted)

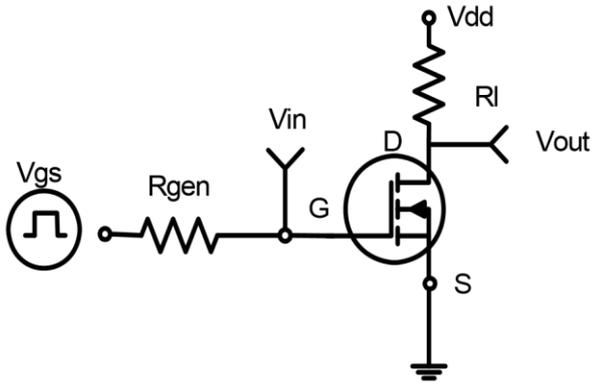
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=250\mu A$	60	68	-	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=60V, V_{GS}=0V$	-	-	1	$\mu A$
Gate-Body Leakage Current	$I_{GSS}$	$V_{GS}=\pm 10V, V_{DS}=0V$	-	$\pm 100$	$\pm 500$	nA
		$V_{GS}=\pm 20V, V_{DS}=0V$	-	$\pm 4$	$\pm 10$	$\mu A$
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	0.7	1.2	1.9	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=5V, I_D=0.4A$	-	1.3	3	$\Omega$
		$V_{GS}=10V, I_D=0.5A$	-	1	2	$\Omega$
Forward Transconductance	$g_{FS}$	$V_{DS}=10V, I_D=0.2A$	0.1	-	-	S
Input Capacitance	$C_{iss}$	$V_{DS}=25V, V_{GS}=0V,$ $F=1.0MHz$	-	21	50	PF
Output Capacitance	$C_{oss}$		-	11	25	PF
Reverse Transfer Capacitance	$C_{rss}$		-	4.2	5	PF
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=30V, I_D=0.2A$ $V_{GS}=10V, R_{GEN}=10\Omega$	-	10	-	nS
Turn-on Rise Time	$t_r$		-	50	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	17	-	nS
Turn-Off Fall Time	$t_f$		-	10	-	nS
Total Gate Charge	$Q_g$	$V_{DS}=10V, I_D=0.3A,$ $V_{GS}=4.5V$	-	1.7	3	nC
Diode Forward Voltage <sup>(Note 3)</sup>	$V_{SD}$	$V_{GS}=0V, I_S=0.2A$	-	-	1.2	V
Diode Forward Current <sup>(Note 2)</sup>	$I_S$		-	-	0.3	A

### Notes:

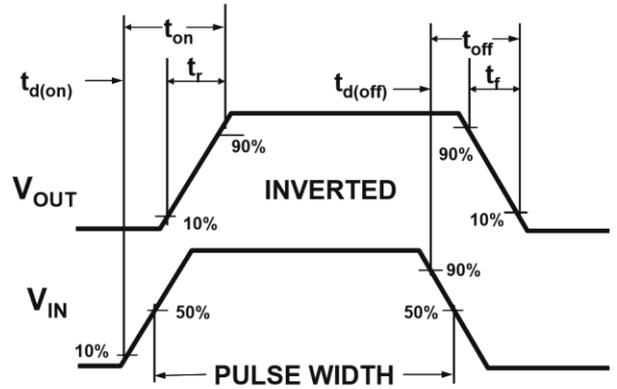
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board,  $t \leq 10$  sec.
3. Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$ .
4. Guaranteed by design, not subject to production

## 60V N-Channel Enhancement Mode MOSFET

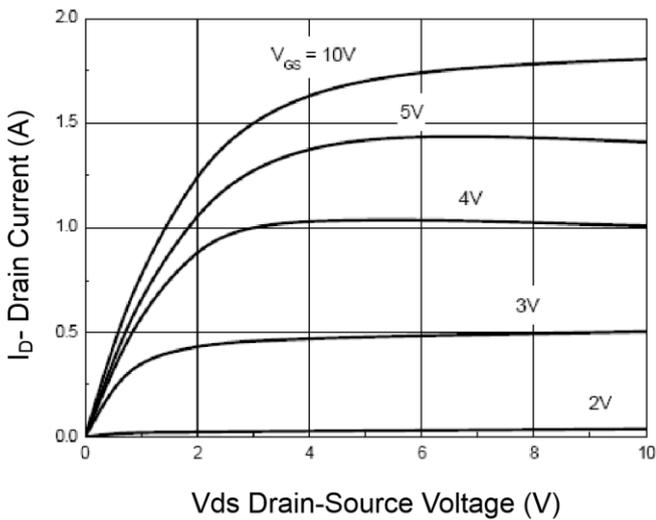
### Typical Electrical And Thermal Characteristics



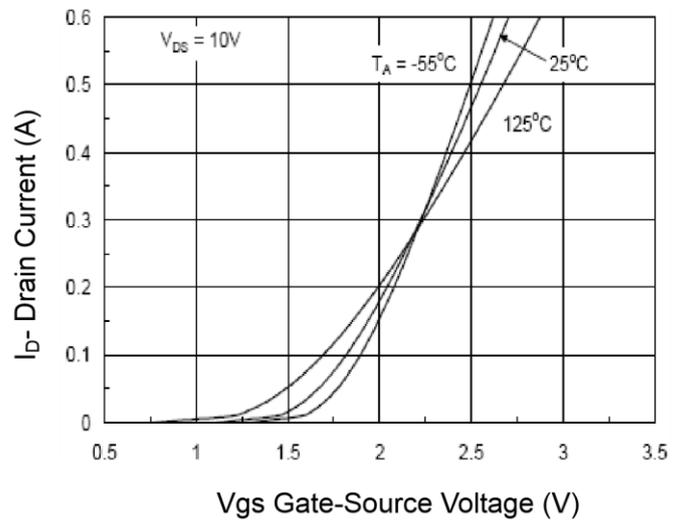
**Figure 1: Switching Test Circuit**



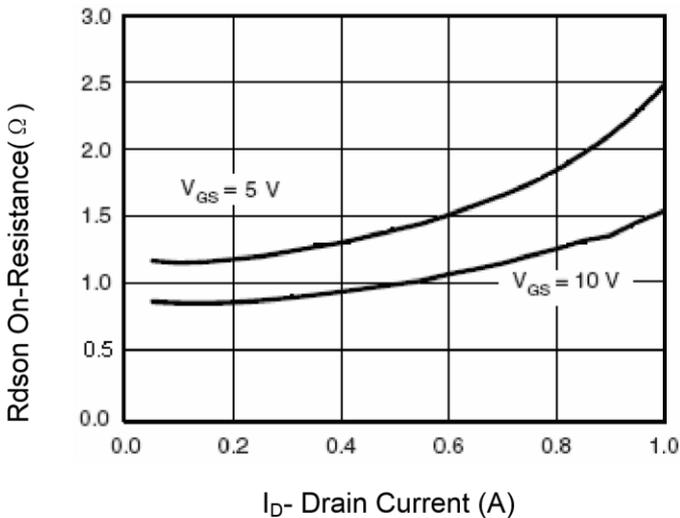
**Figure 2: Switching Waveforms**



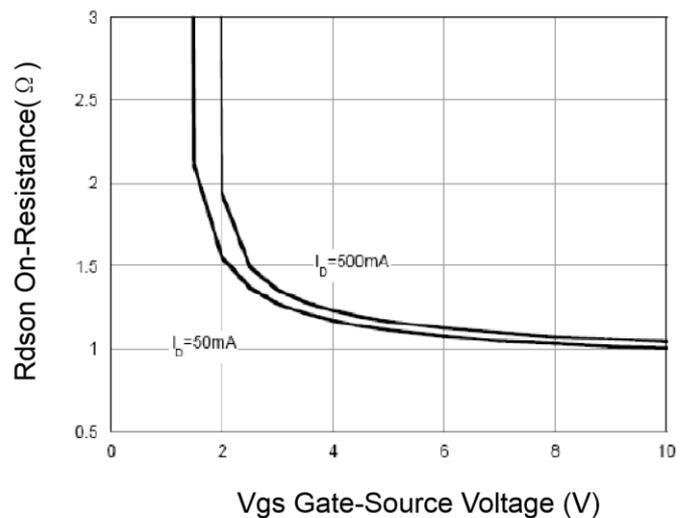
**Figure 3 Output Characteristics**



**Figure 4 Transfer Characteristics**



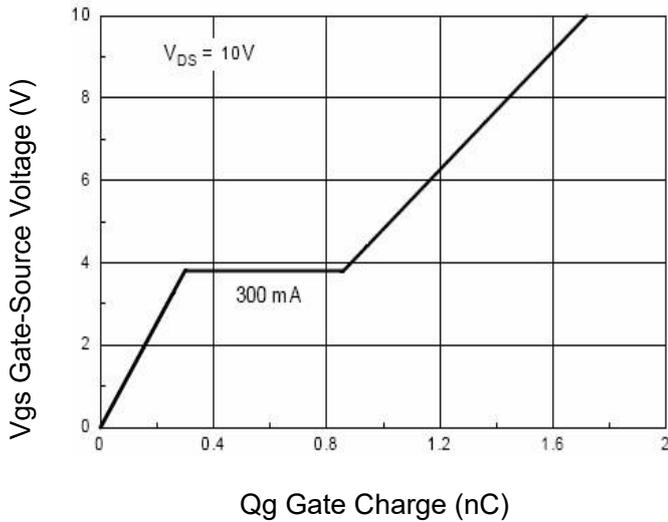
**Figure 5 Drain-Source On-Resistance**



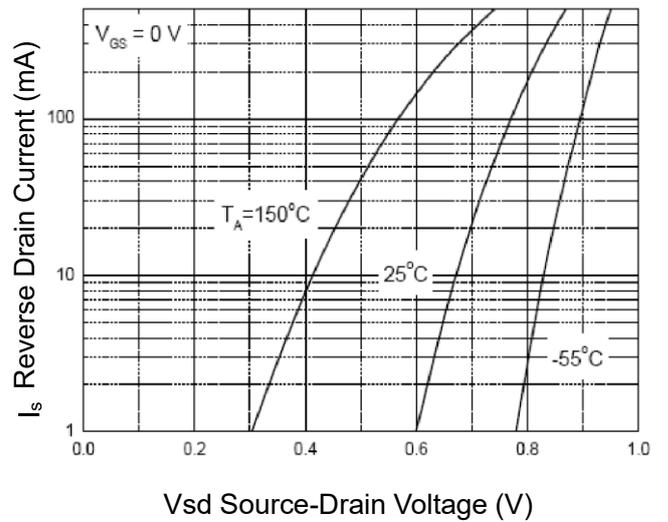
**Figure 6 Rdson vs Vgs**



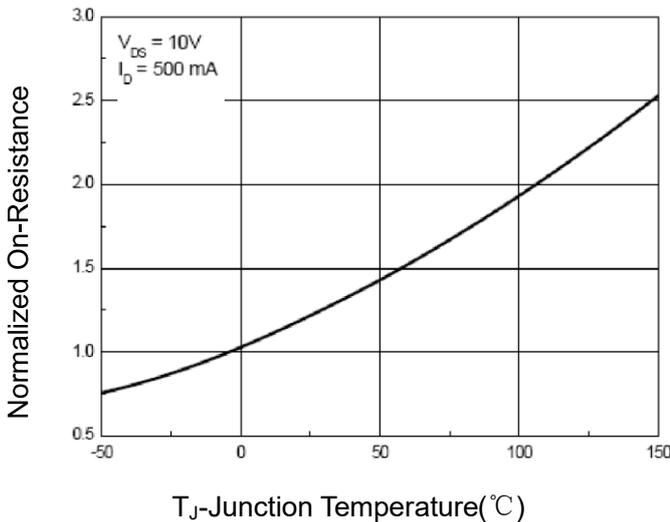
## 60V N-Channel Enhancement Mode MOSFET



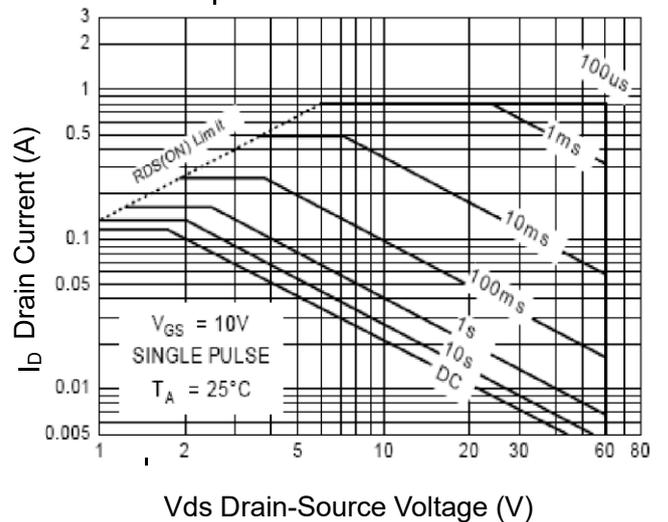
**Figure 7 Gate Charge**



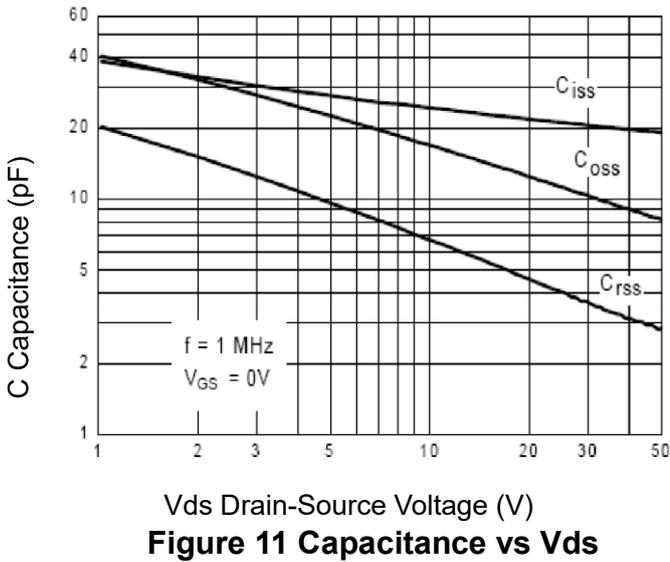
**Figure 8 Source-Drain Diode Forward**



**Figure 9 Drain-Source On-Resistance**

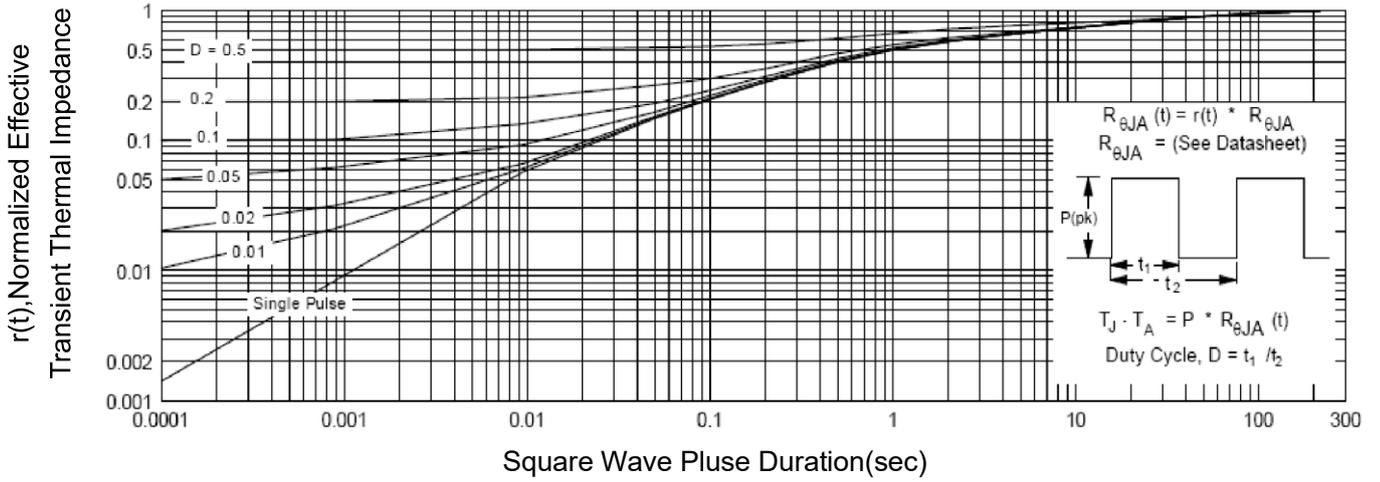


**Figure 10 Safe Operation Area**



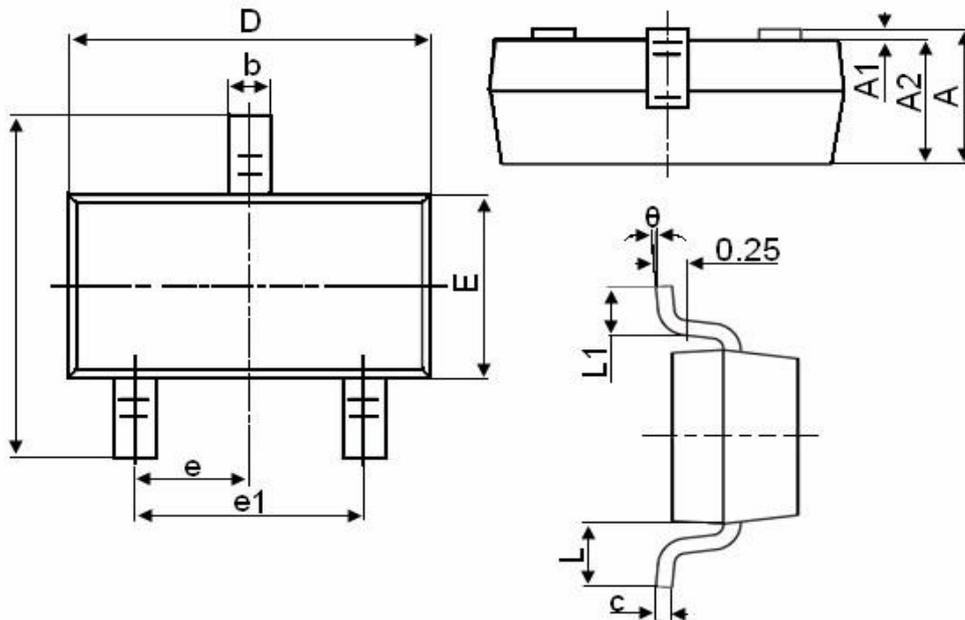
**Figure 11 Capacitance vs Vds**

**60V N-Channel Enhancement Mode MOSFET**



**Figure 12 Normalized Maximum Transient Thermal Impedance**

### SOT-23 Package Information



Symbol	Dimensions in Millimeters	
	MIN.	MAX.
A	0.900	1.150
A1	0.000	0.100
A2	0.900	1.050
b	0.300	0.500
c	0.080	0.150
D	2.800	3.000
E	1.200	1.400
E1	2.250	2.550
e	0.950TYP	
e1	1.800	2.000
L	0.550REF	
L1	0.300	0.500
θ	0°	8°

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